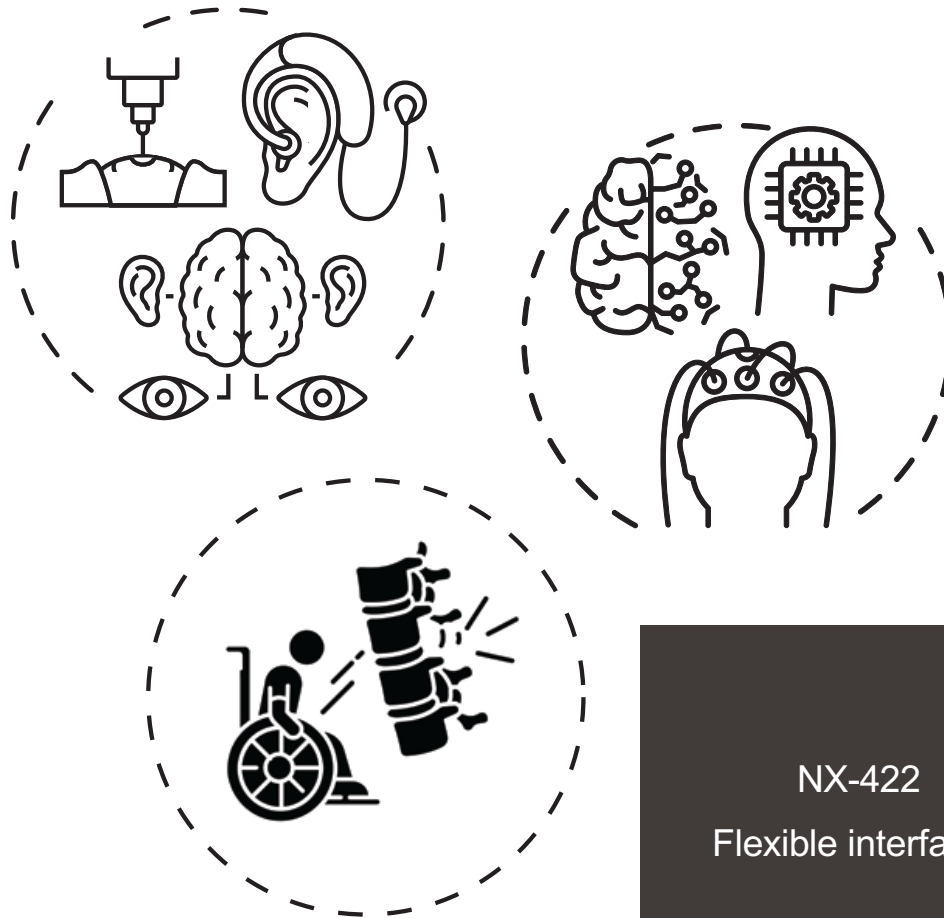




Neural Interfaces

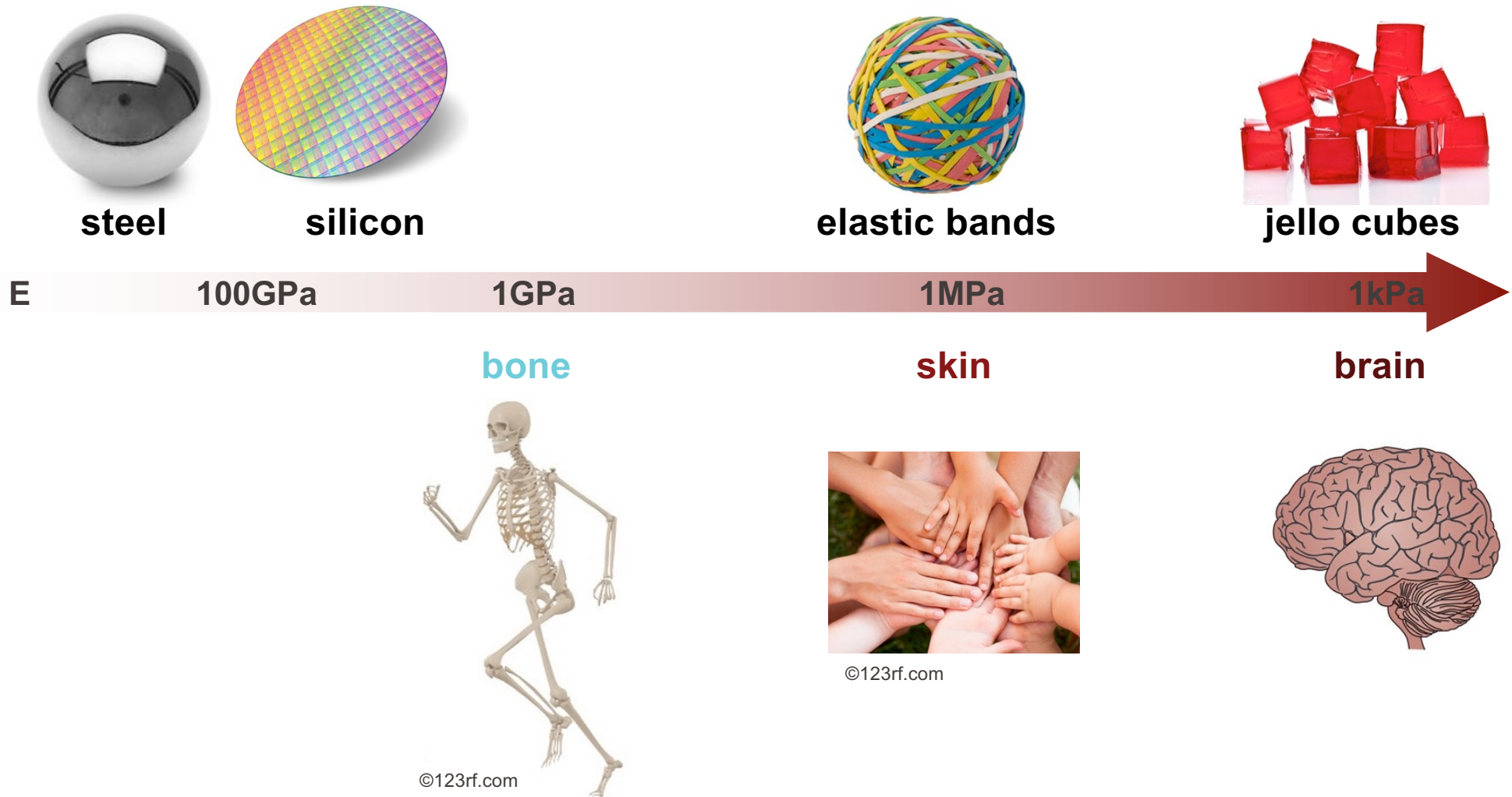
NX-422
Flexible interfaces

Stéphanie P. Lacour
Neuro-X Institute

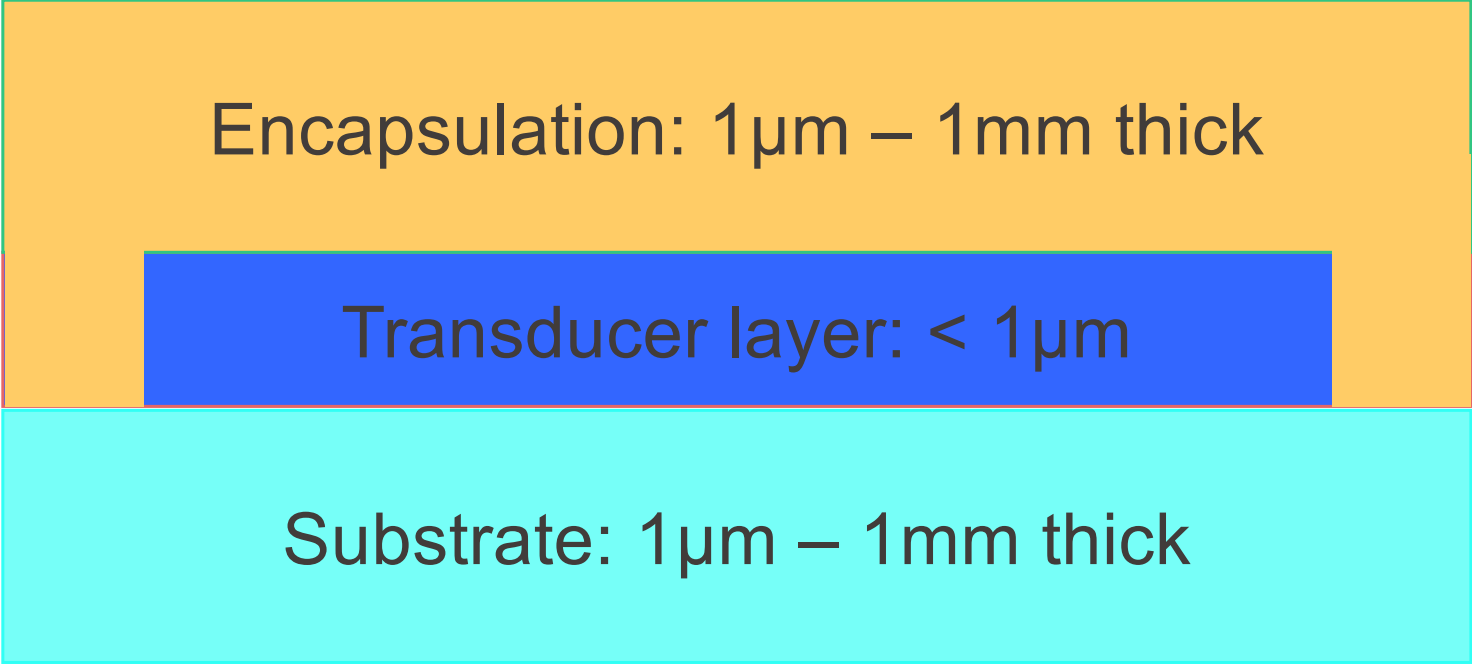
Brain computer interfaces

- Overview
- Silicon-based neurotechnology
- **Flexible implantable neurotechnologies**

Man-made vs biological materials



Flexible implantable interfaces



Encapsulation: $1\mu\text{m} - 1\text{mm}$ thick

Transducer layer: $< 1\mu\text{m}$

Substrate: $1\mu\text{m} - 1\text{mm}$ thick

Desired properties for a flexible substrate

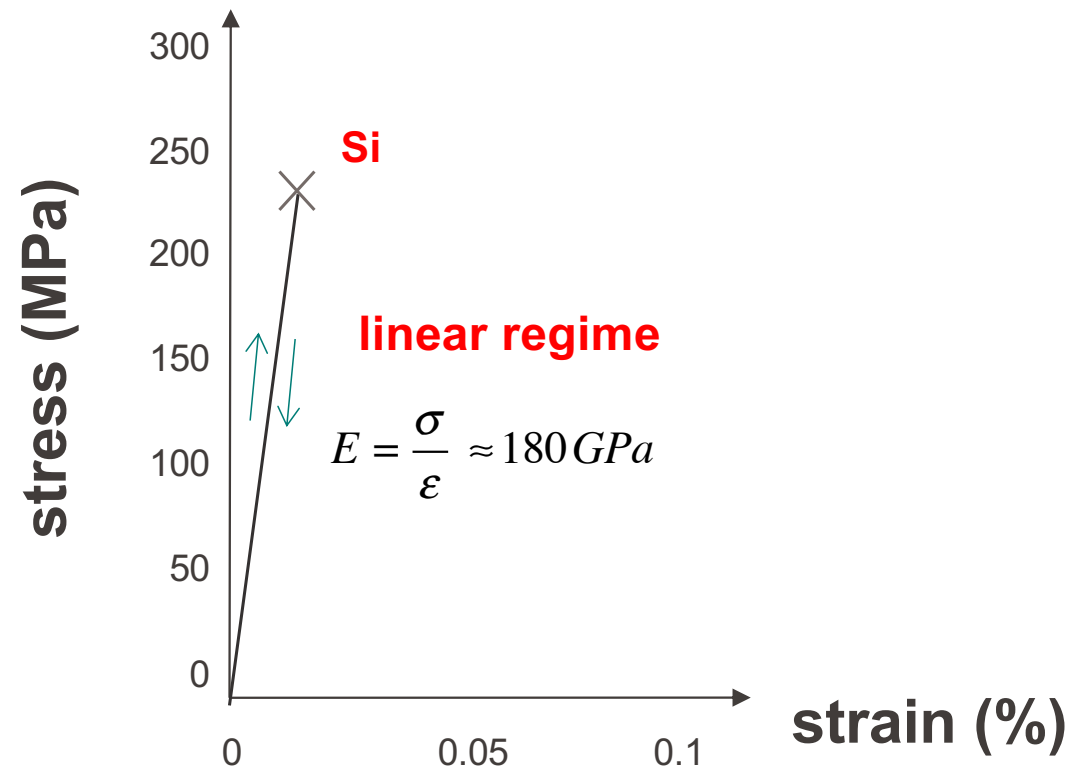
- **Physical**
 - Smoothness
 - Barrier properties / hermeticity
 - Dimensional stability
 - High robustness
 - Mechanical strength/flexibility
- **Thermal stability**
- **Optical transparency**
- **Dielectric properties**
- **Biocompatibility / biodegradability**

Thin = flexible

cellulose



<http://www.paperonweb.com/>



- The critical strain is the maximum applied strain before mechanical fracture

material property
Brittle glass: <0.2%
Ductile metal: <20%

$$\epsilon_{crit} = \pm \frac{h}{2 R_{0,min}}$$

design parameter
10µm to 250µm

application driven
1mm to cm

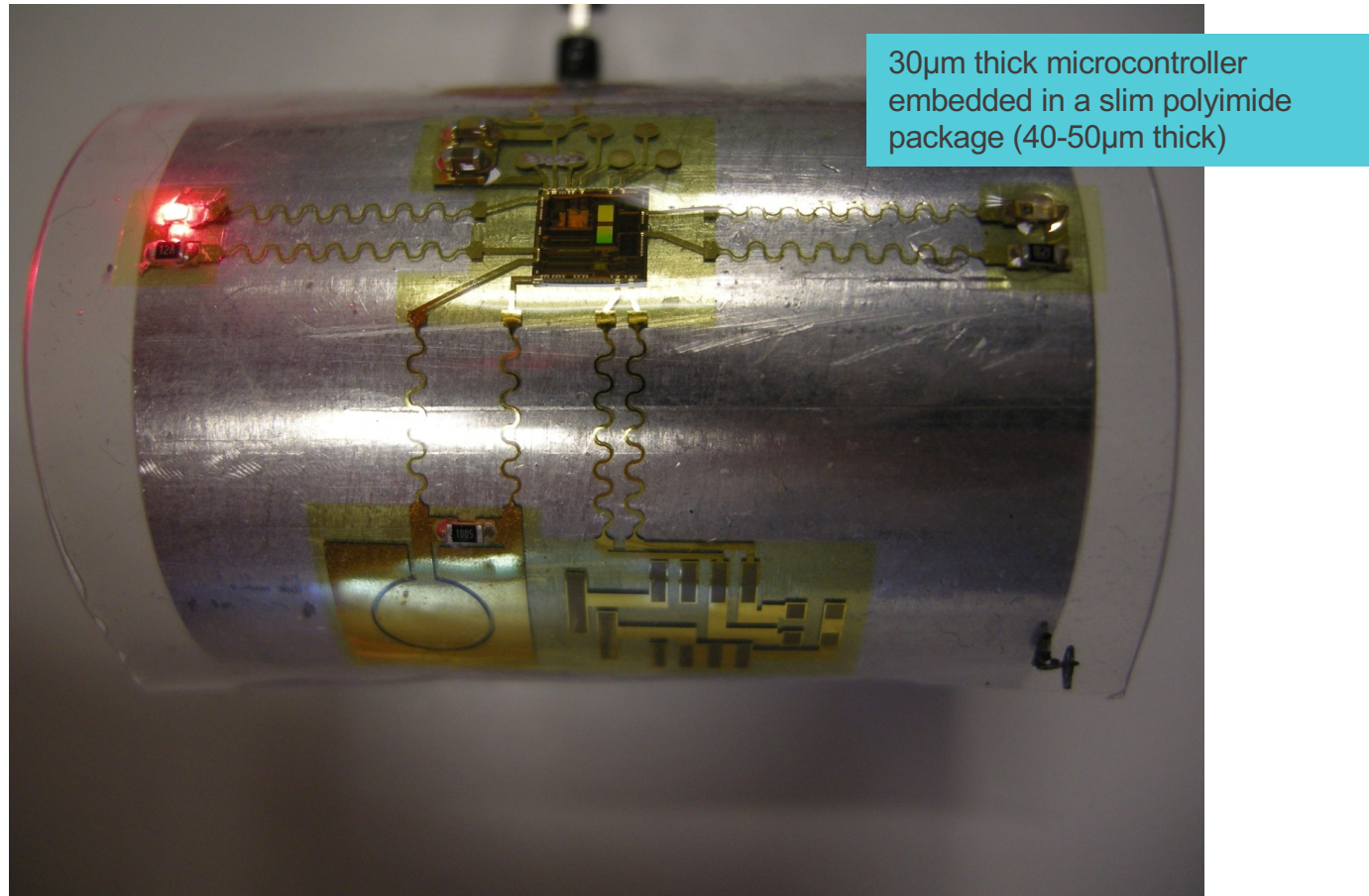
Example: The critical strain is 0.5%; the application requires a 1cm min. bending radius. How thick should the substrate be?

a. 50µm

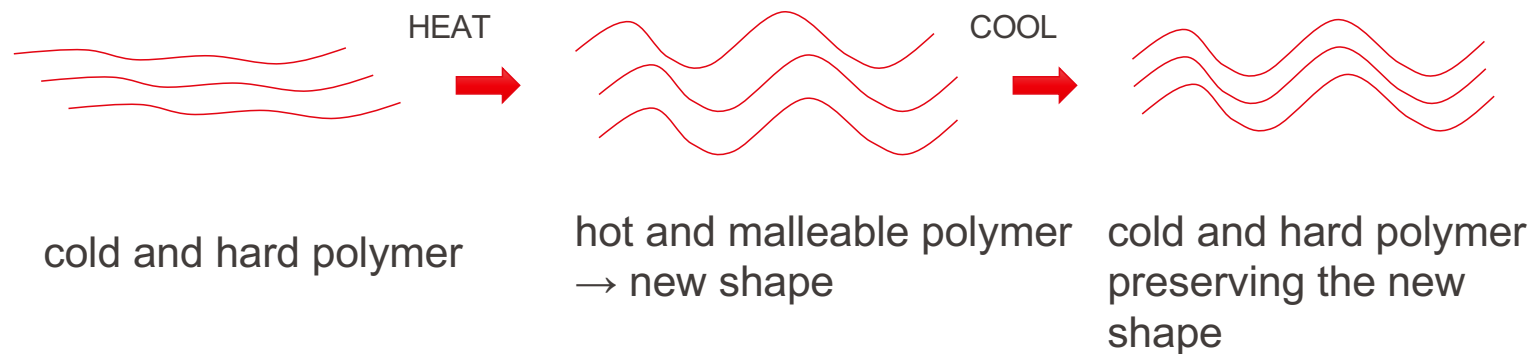
b. 100µm

c. 1mm

Ultra-thin flexible chip

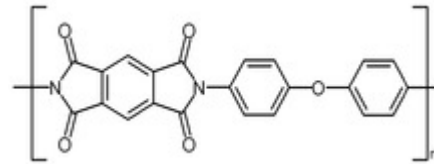


- A polymer prepared with linear or ramified chains.
 - Chains are weakly linked (Van der Waals or hydrogen bonds)



- A material, which softens and hardens reversibly on heating and cooling

Polyimide films



Kapton®



- **Imide-based polymer**

- Imide: 2 acyl groups bonded to nitrogen

- **Thermoplastic**

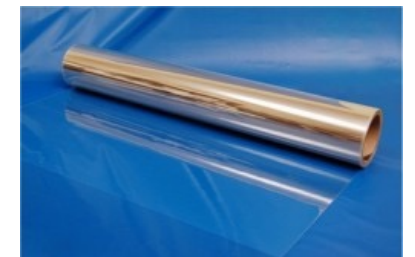
- Available as a foil
- Spinable as an uncured resin
- Can be photosensitive



- **Good thermal and mechanical stability**

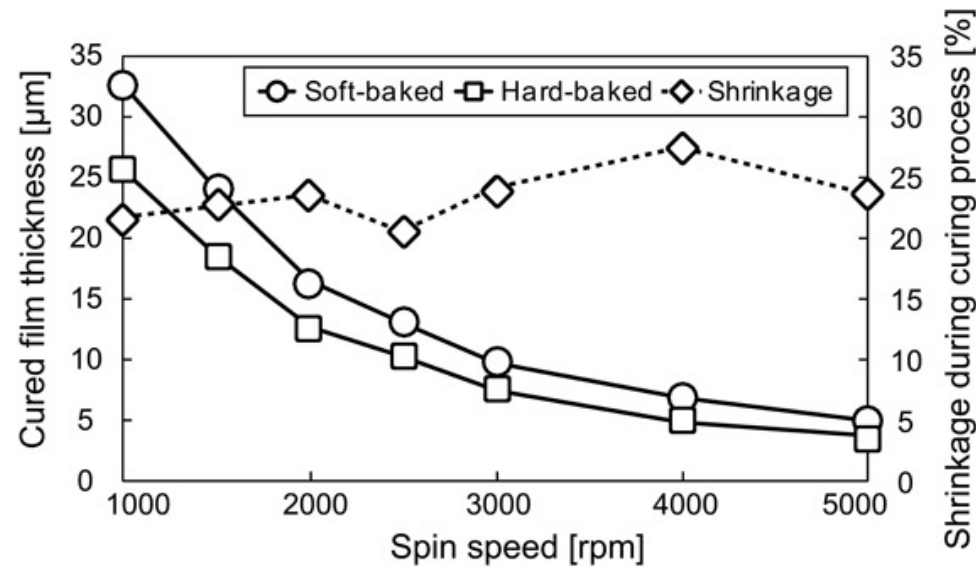
- Young's modulus: ~2.5 GPa
- CTE: 20 – 60 ppm/°C

- **High resistance to solvents and weak acids**

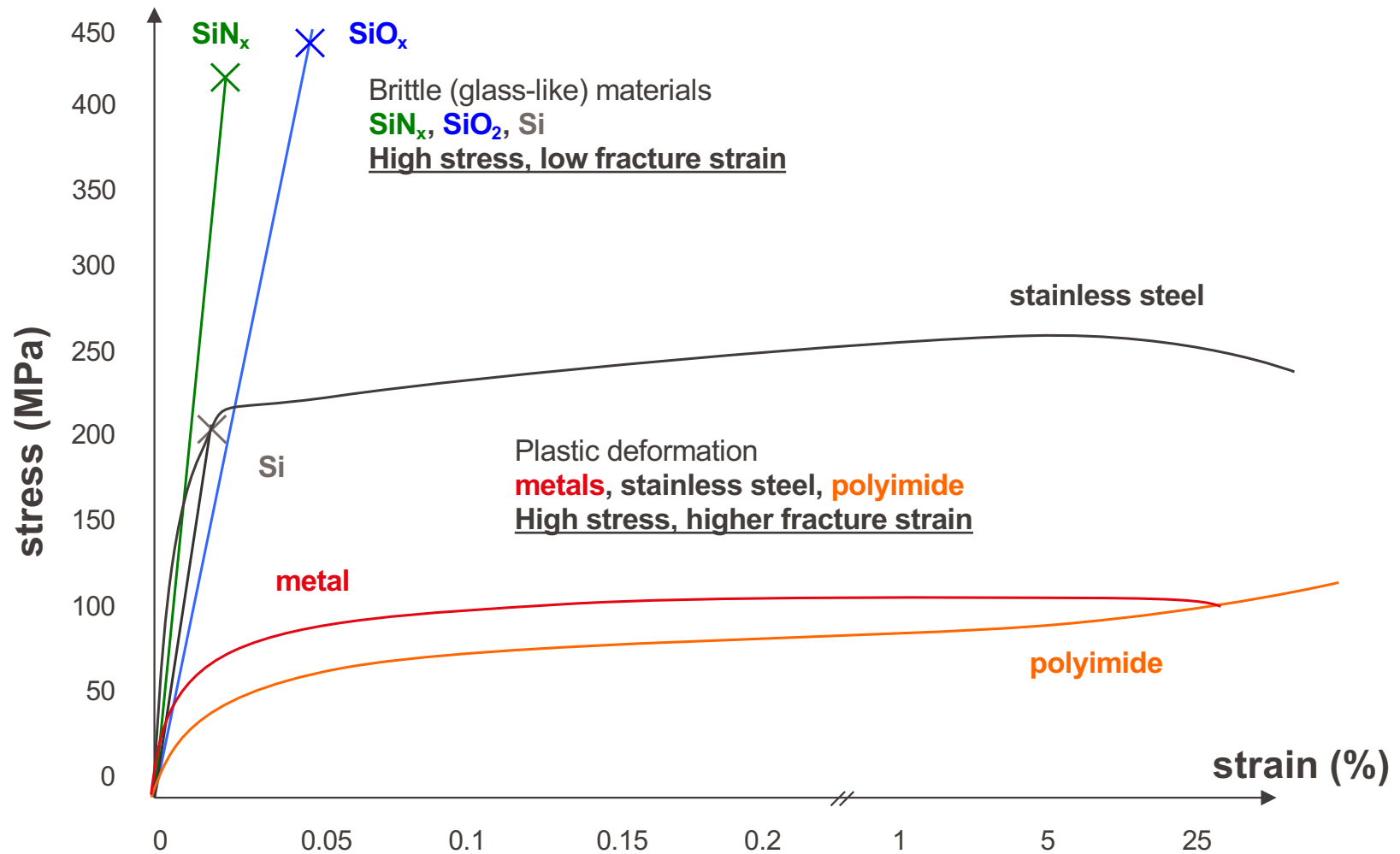


Forming a polyimide film

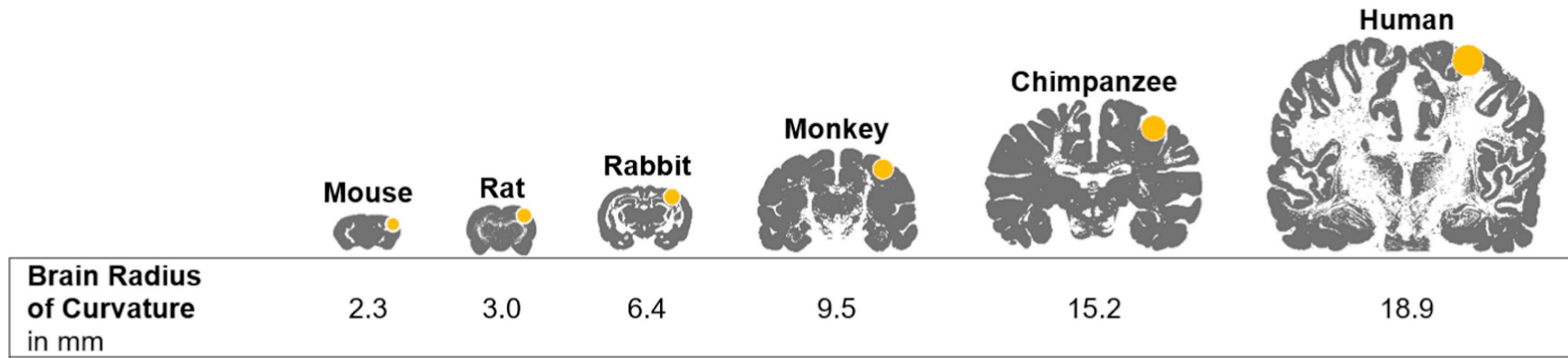
- 1. clean the rigid carrier e.g. a silicon or glass slide
- 2. spin-coat polyimide
 - Spin speed → thickness
 - Ramps → uniformity and edge beads
 - Soft bake



Typical stress(strain) responses



Conformability and bending stiffness



Elastic modulus and thickness control the compliance of the device.

Bending stiffness

$$D = \frac{Eh^3}{12(1-\nu^2)}$$

elastic modulus

thickness

$$E_{PI} \sim 1-5 \text{ GPa}$$

- Electrical conductors

- **Physical properties**

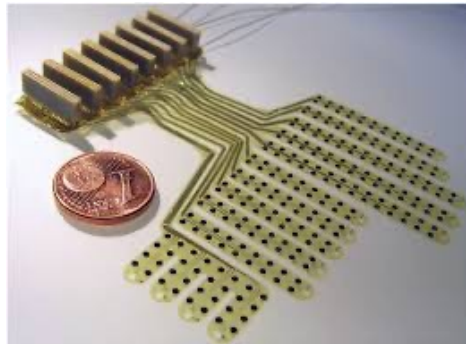
▪ Electrical conductivity/resistivity	σ/ρ	S/cm or $\Omega\cdot\text{cm}$
▪ Thermal conductivity	k	W/m. $^{\circ}\text{C}$
▪ Thermal coefficient of resistance	TCR	ppm/ $^{\circ}\text{C}$
▪ Coefficient of thermal expansion	CTE	ppm/ $^{\circ}\text{C}$
▪ Young's modulus	E	MPa-GPa

- **Process ability**

- Deposition
 - Patterning

Interconnect resistance

Flexible ECoGs
T. Stieglitz's lab



$$R = \rho \frac{L}{t W} \quad [\Omega]$$

material	Resistivity [Ω/cm] for THIN film
Ag	$\sim 20 \mu\Omega.\text{cm}$
Al	$\sim 3 \mu\Omega.\text{cm}$
Pt	$\sim 10 \text{ s } \mu\Omega.\text{cm}$

Microfabrication of electrode array on polyimide substrate

Option 1

- Prepare the carrier substrate
- Deposit the metal film
- Pattern the metal film
- Deposit and pattern encapsulation film

Option 2

- Prepare the carrier substrate
- Pattern a masking film
- Deposit the metal film
- Remove the masking film
- Deposit and pattern encapsulation film

Process flow for a thin metal track

Option 1



1. Spin-coat the substrate polymer
Material and thickness
2. Evaporate metal
Material and thickness
3. Photolithography
*Mask preparation, photoresist spin-coating & baking
Curing, development*
4. Metal etching
Dry or wet process
5. Photoresist lift-off
Wet process

Process flow for a thin metal track

Option 1



6. spin-coat top encapsulation film
material and thickness



7. pattern encapsulation film
etching method and thickness



8. sample release

Encapsulation: $1\mu\text{m} - 1\text{mm}$ thick

Transducer layer: $< 1\mu\text{m}$

Carrier: $1\mu\text{m} - 1\text{mm}$ thick

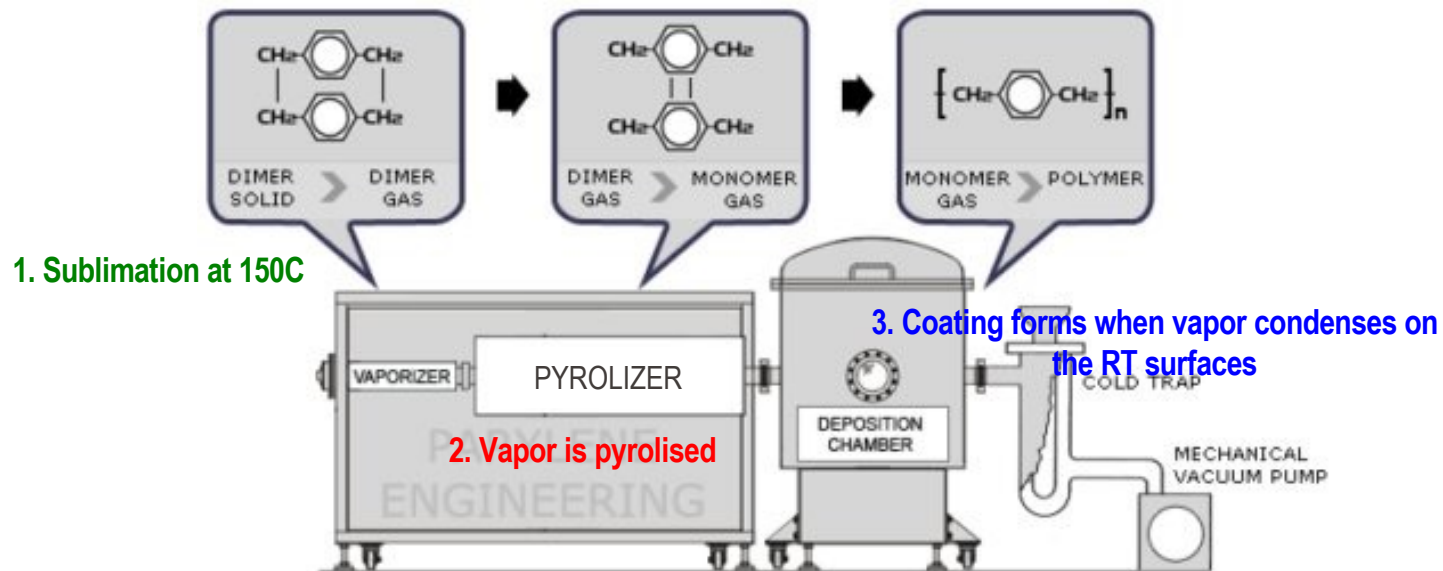
Encapsulation materials

- Polymers identical to the substrate
- Alternative polymers
- Inorganic thin films such as oxides, nitrides, etc.

Vapor phase processed plastics

■ Parylenes: poly-para-xylylenes

- linear, highly-crystalline polymers produced as films or coatings
- Vapor deposition polymerization
- Insulating thermoplastic with high degree of chemical inertness



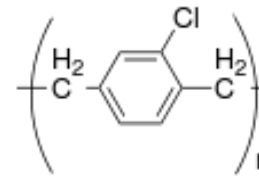
www.paryleneengineering.com

Parylene: conformal coating

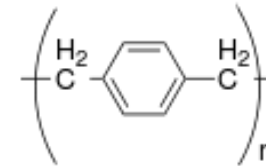


Types of parylenes

- Parylene C → standard compound



- **Parylene N → biomed. applications**



- Parylene D → higher temperature applications
- Parylene HT → high temperature and UV exposure stability

- **Mechanical properties**

- Young's modulus: 0.5GPa – 2.75GPa
- Low stress coating that does not form sites prone to crack initiation

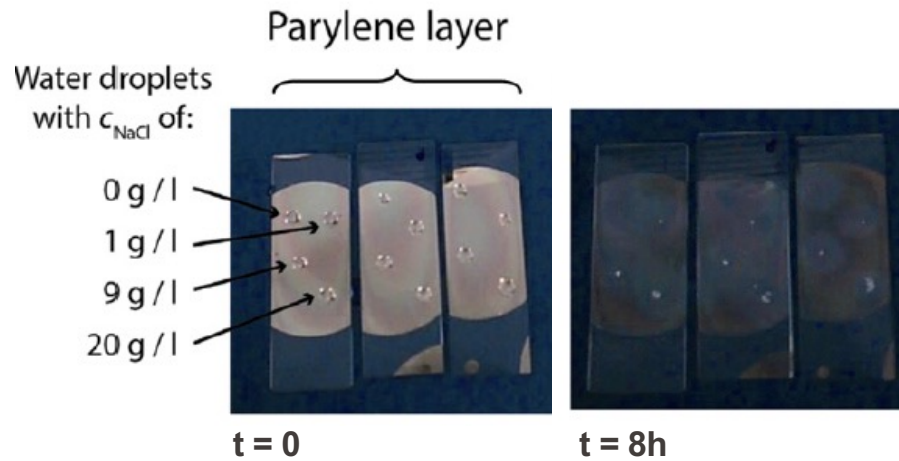
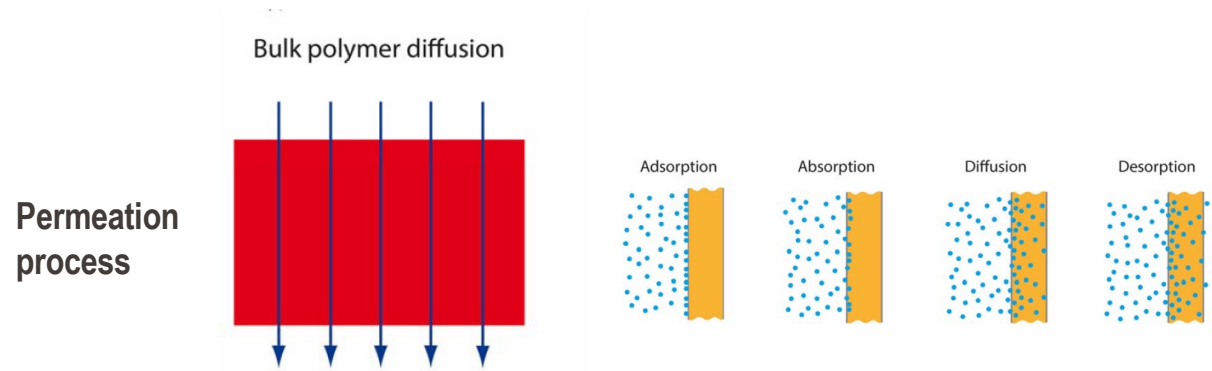
- **Thermal stability**

- CTE: **35 – 70** ppm/°C

- **Optical properties**

- Transparent and colorless in the visible range
- Autofluorescence – limited

Hermeticity



Test : Calcium mirror test

Water Vapor Transmission Rate (Par C)
 $\text{WVTR} \sim 10^{-2} \text{ g/m}^2/\text{day}$

WVTR

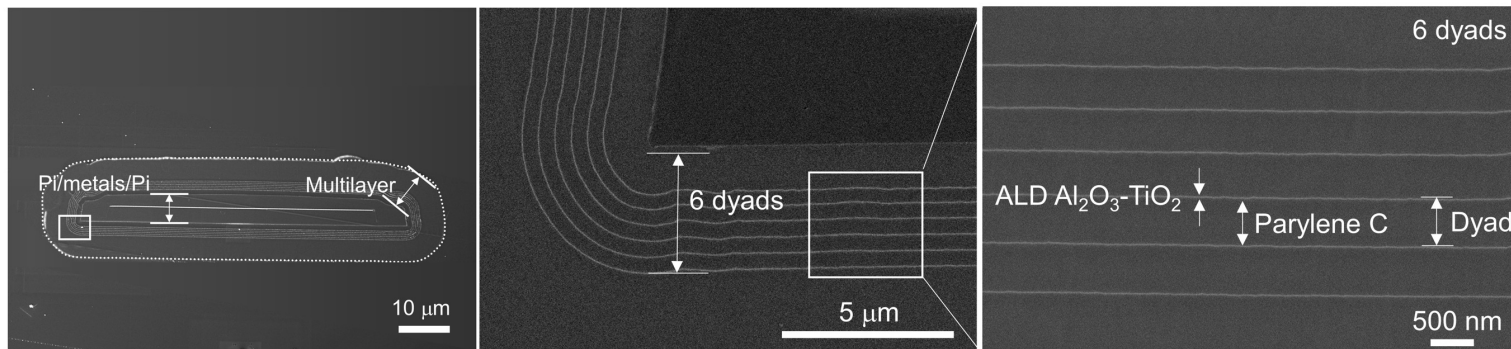
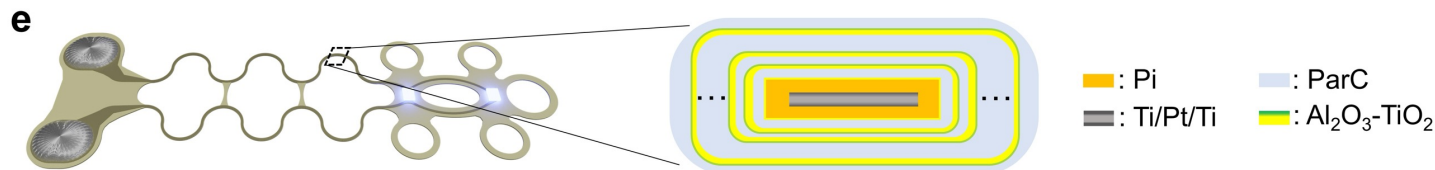
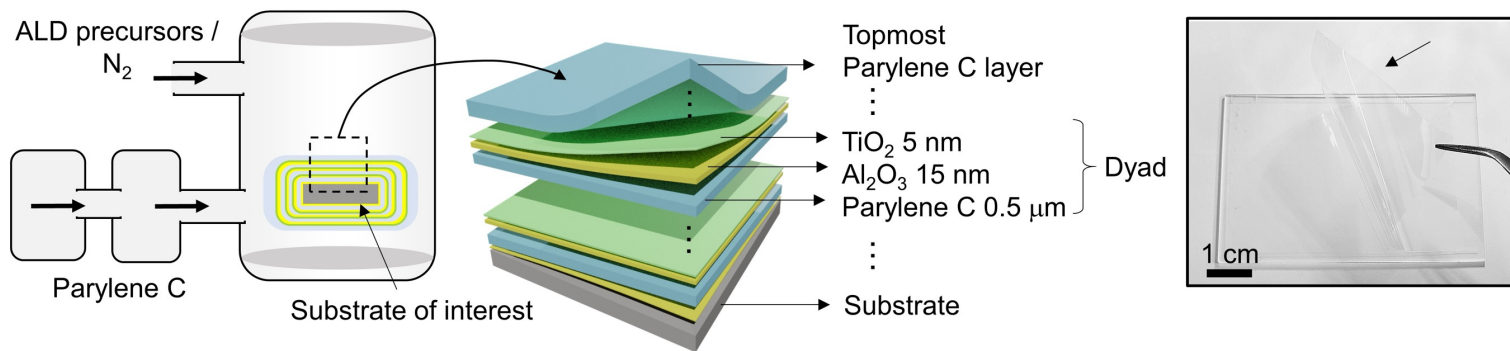
Thin Film Encapsulation

- Stable operation of flexible electronic devices
 - >10,000 h requires $10^{-3} \leq \text{WVTR} \leq 10^{-6} \text{ g m}^{-2} \text{ d}^{-1}$
 - Even more constraining for implantable devices

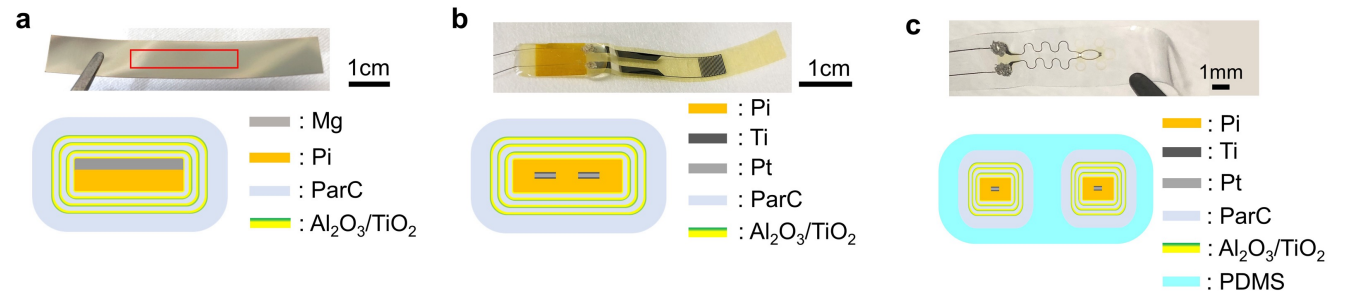
- Thermoplastics

- Single-layered barrier films
 - e.g. SiO_x , SiN_x , SiC_x , SiO_xN_y , SiO_xC_y , Al_2O_3 , AlO_xN_y , ZrO_2 , TiO_2 , MgO , ZnO , SnO_2
 - relatively high $10^{-1} \leq \text{WVTR} \leq 10^{-3} \text{ g m}^{-2} \text{ d}^{-1}$

Organic/inorganic multilayer encapsulation



Lifetime evaluation



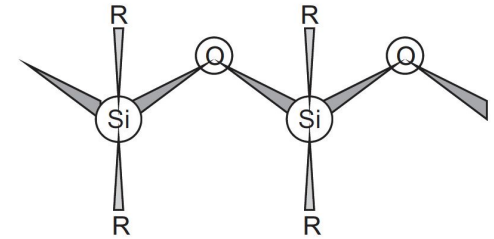
Mg test

IDE: Inter-digitated electrodes

OE: micro-LED

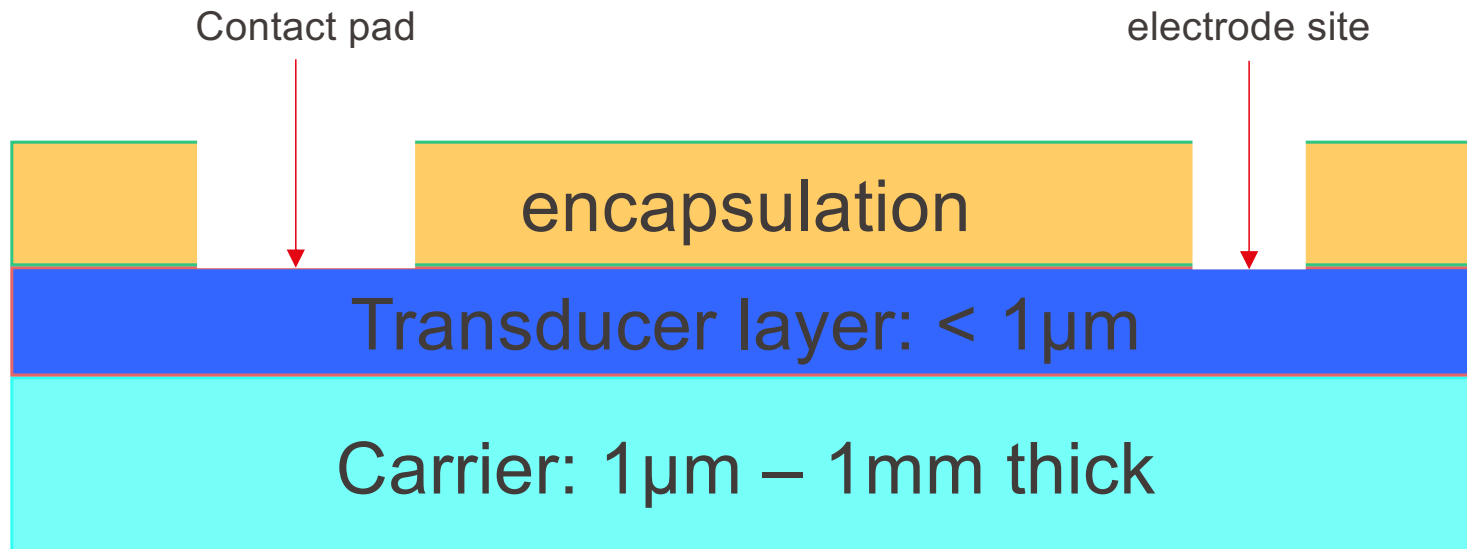
Silicones

encapsulation / packaging



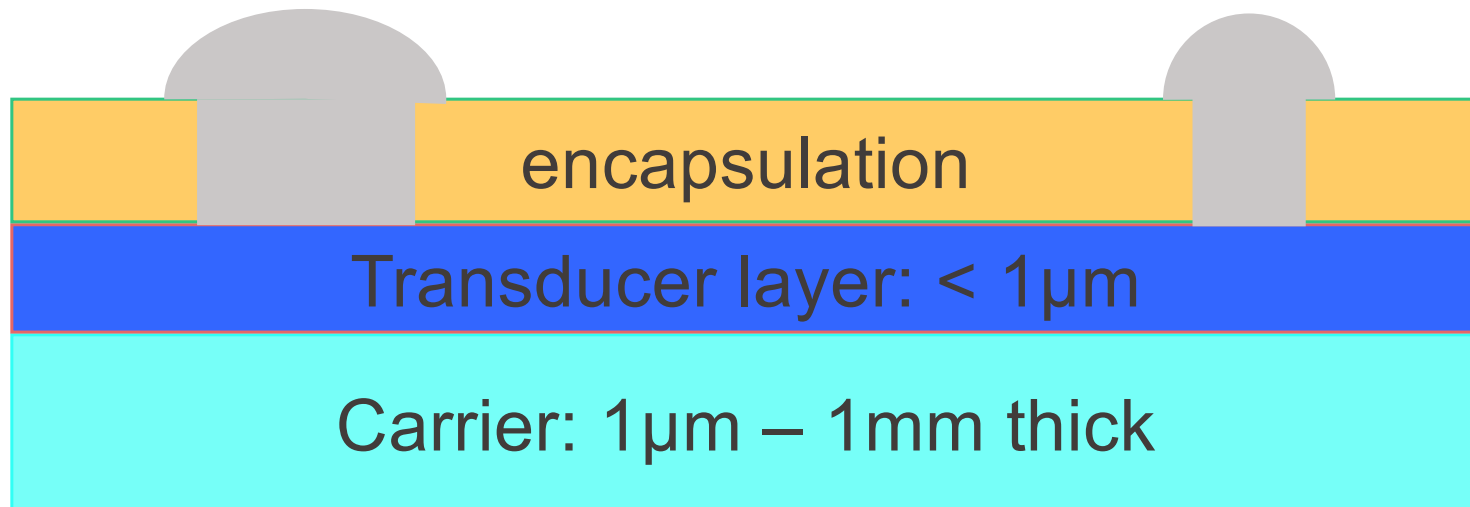
- Long-lasting material
- **Polymer** with simultaneous presence of organic groups attached to inorganic atoms
- Silicone elastomers (rubbers)
 - Molding, injection, spin-coating, printing
 - Cross-linked polymer
- Soft polymer : elastic modulus range: 10 kPa – 10 MPa
- Very good protection over corrosion of silicon and oxidizable materials
- Very good electrical insulators (esp. Fluoropolymers)

Encapsulation patterning



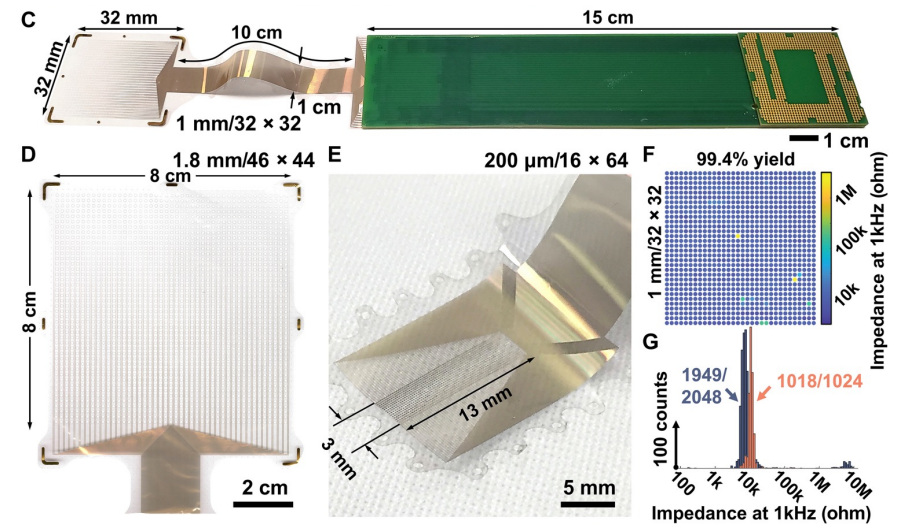
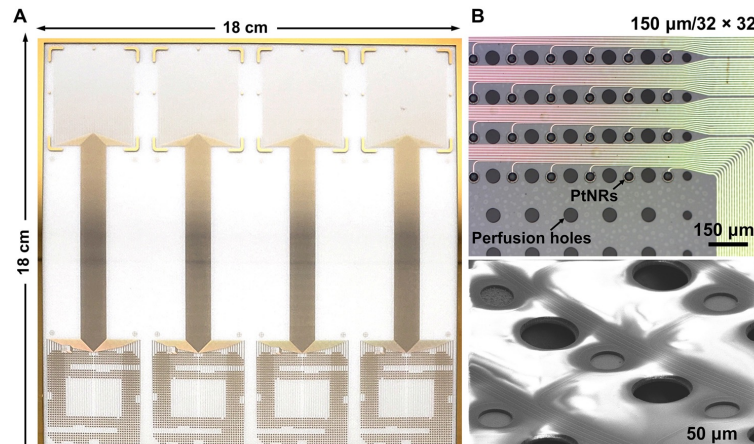
Conductive coating

- Conductive paste
- Conductive composite
- Electrodeposited material: metal or organic conductors



Thin film electrode arrays

- Multithousand-channel PtNRGrid ECoG arrays
 - 8 cm by 8 cm (2048 channels)
 - 30 μm wide PtNR contacts recessed by $\sim 2 \mu\text{m}$ below the surface of Par-C



Mechanical design of flexible thin-film devices



Young's modulus, thickness

Film: E_f , d_f

Substrate: E_s , d_s

$$E_f \cdot d_f \ll E_s \cdot d_s$$

The substrate dominates;
The film complies with it.

Ex. Film on glass

$$E_f \cdot d_f \approx E_s \cdot d_s$$

Equal strength of film and
substrate

Ex. Film on plastic

$$E_f \cdot d_f \gg E_s \cdot d_s$$

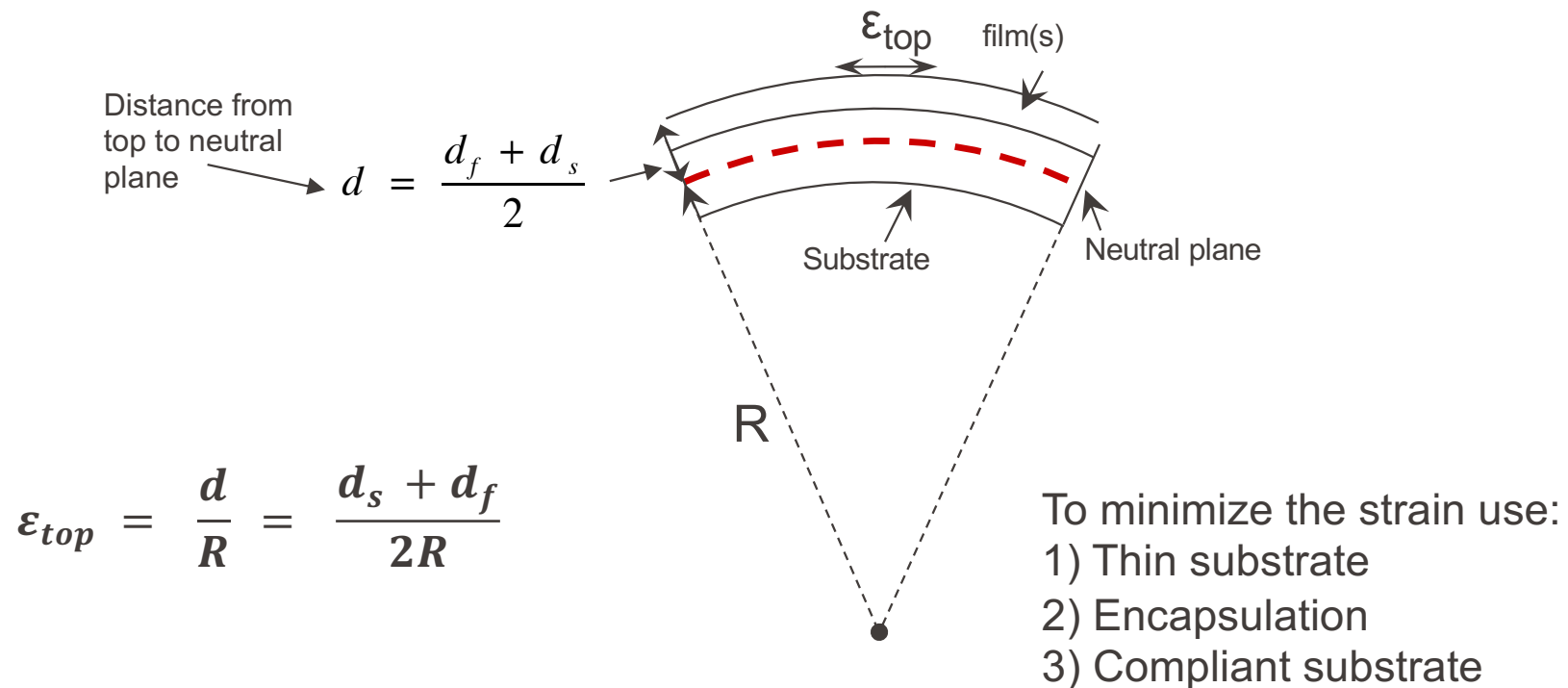
The film dominates,
The substrate complies with it

Ex. Film on rubber

Bending a film-on-substrate stack

Stiff substrates

$$E_f \cdot d_f \ll E_s \cdot d_s \quad (\text{often } d_f \ll d_s)$$



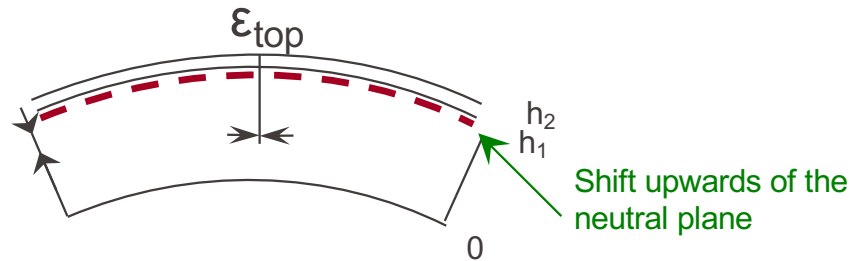
Bending a film-on-substrate stack

Compliant substrates

$$E_f \cdot d_f \approx E_s \cdot d_s$$

Distance from
top to neutral
plane

$$d < \frac{d_f + d_s}{2}$$



In pure bending mode, the neutral plane is located at the “weighted average” of the mid-points of each layer

mid-point of each layer
$$h_{mi} = \frac{h_i + h_{i+1}}{2} = h_i - \frac{d_i}{2}$$

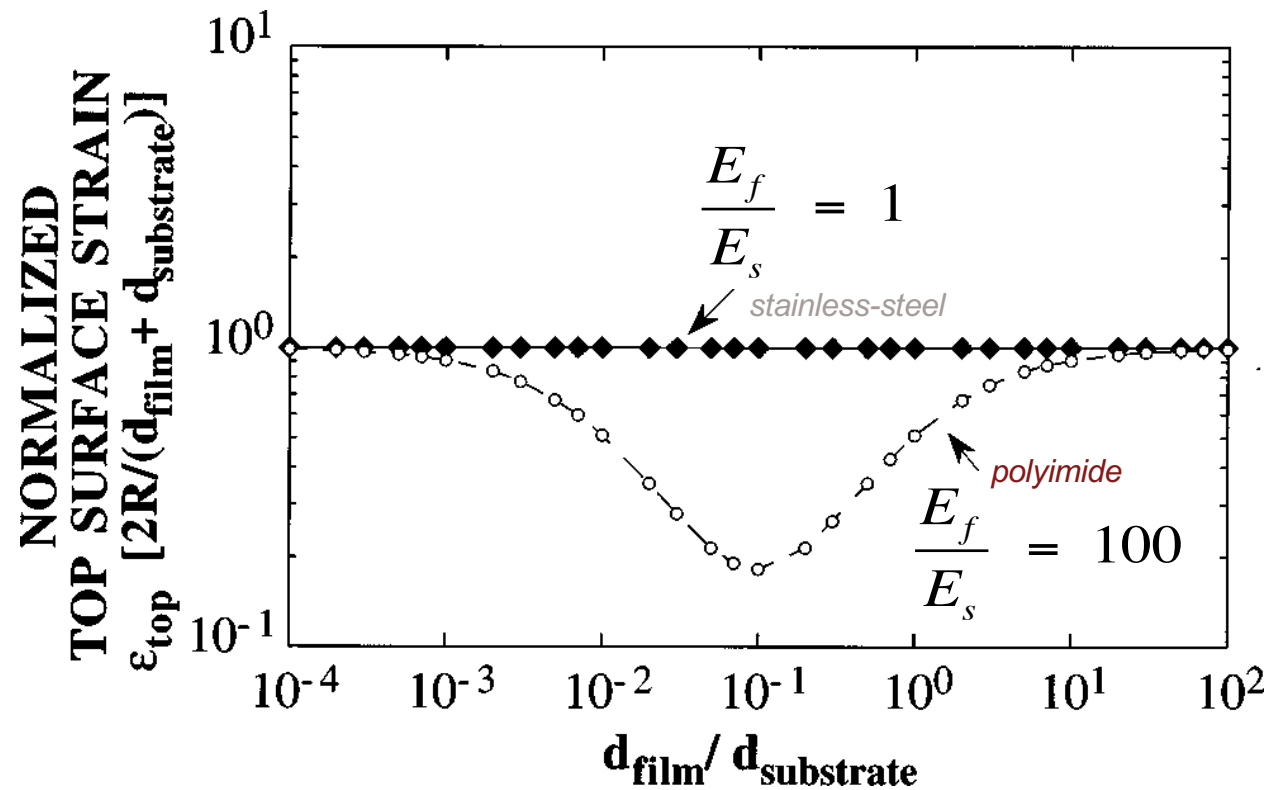
Strain at the top surface

- Case: Thin film f bonded to substrate s
 - d_f thickness
 - R bending radius

$$\varepsilon_{top} = \left(\frac{d_s + d_f}{2R} \right) \frac{1 + 2\eta + \chi\eta^2}{(1 + \eta)(1 + \chi\eta)} \quad \text{with} \quad \begin{aligned} \eta &= d_f / d_s \\ \chi &= E_f / E_s \end{aligned}$$

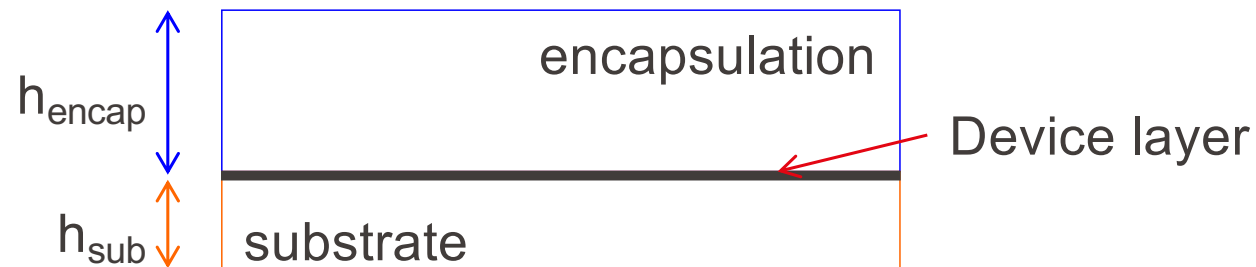
Film on compliant substrate

Strain in the film as a function of film/substrate thickness ratio



Z. Suo et al, 1999, Applied Physics Letters, 74 8, 1177-1179.

Placing devices in the neutral plane

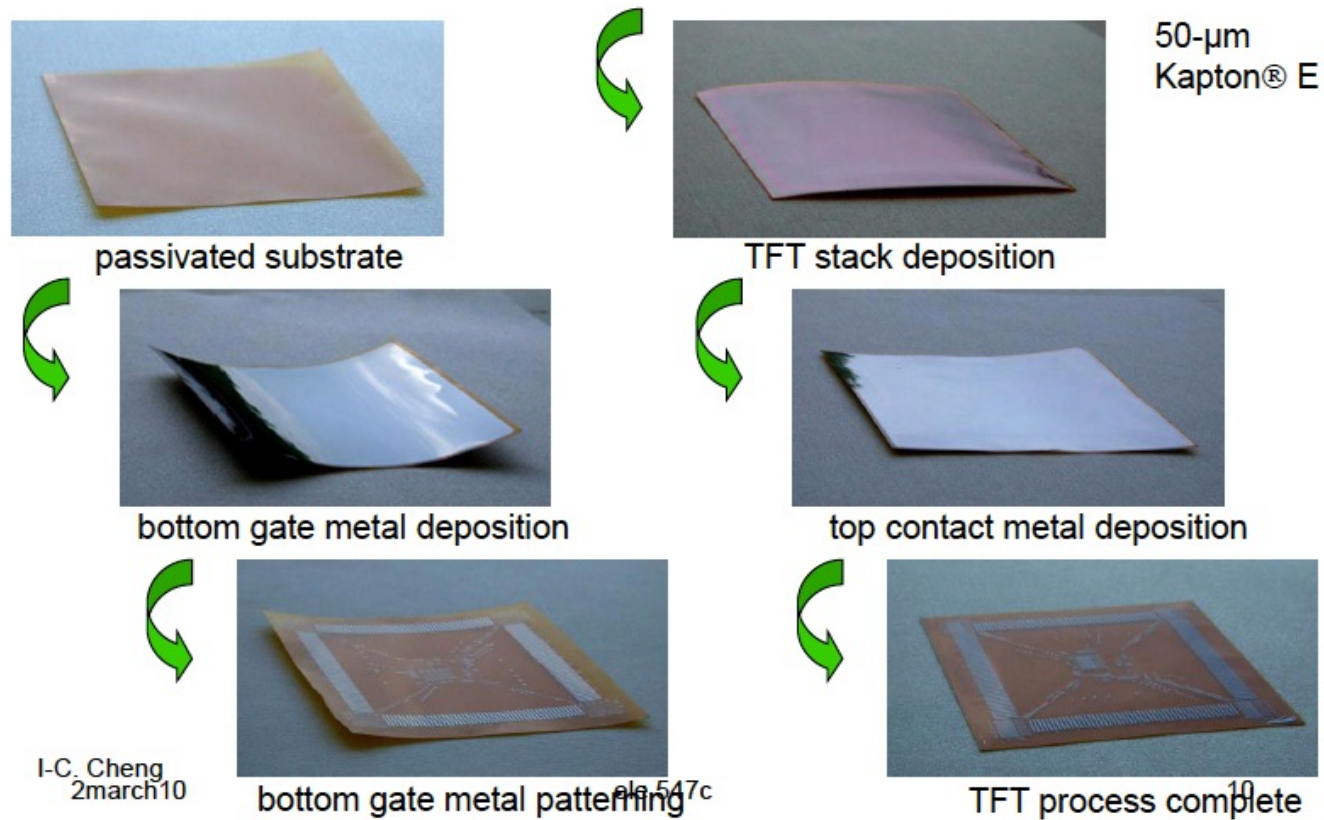


Design rule: place the device layer at the **neutral surface**

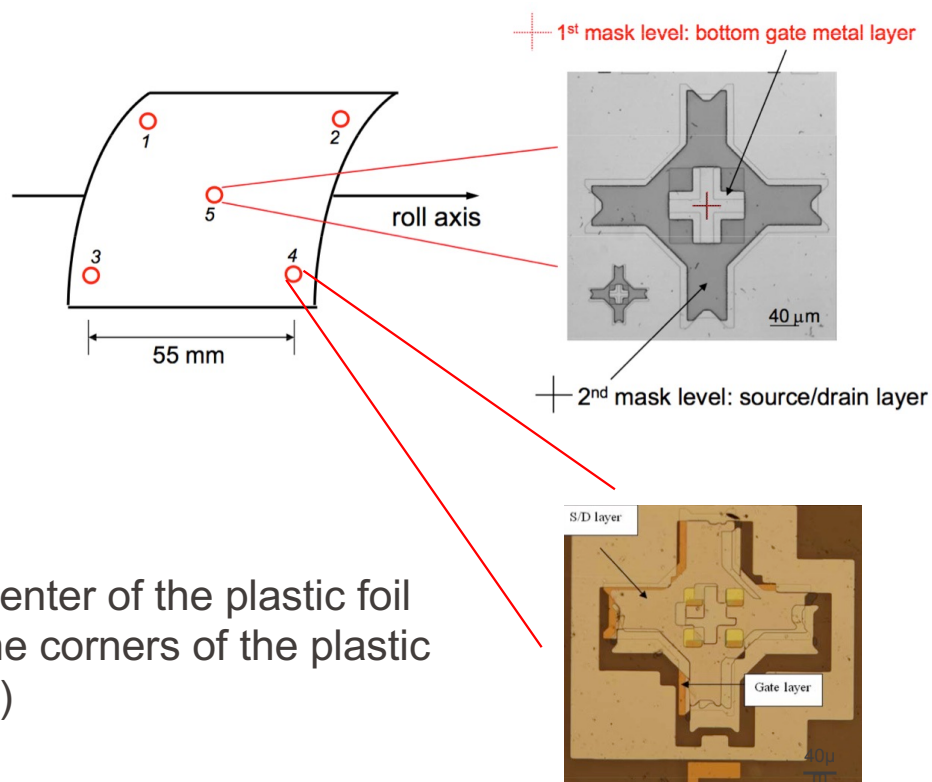
Brain computer interfaces

- Overview
- Silicon-based neurotechnology
- **Flexible implantable neurotechnologies**
 - **Challenges in microfabrication on flexible substrates**

Curvature during manufacturing



*α -Si:H TFTs on Kapton foil
I-C Cheng, Princeton University*



- ⇒ Aligned at the center of the plastic foil
- ⇒ Misaligned at the corners of the plastic foil ($\approx 1000\text{ppm}$)

- Microfabrication
 - Borrowed from microelectronics processing
 - Thin-film processing
- Miniaturisation and reproducibility
 - High density electrode array
 - Active electrode array